

UT3414

N-CHANNEL ENHANCEMENT MODE

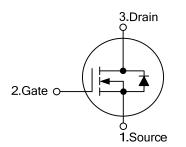
DESCRIPTION

The **UT3414** uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications.

FEATURES

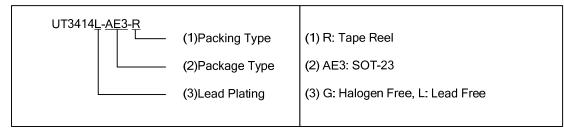
- * $R_{DS(ON)}$ < 50m $\Omega @V_{GS}$ = 4.5V
- * $R_{DS(ON)}$ < 63m Ω @V_{GS} = 2.5V
- * $R_{DS(ON)}$ < 87m $\Omega @V_{GS}$ = 1.8V
- * Low capacitance
- * Low gate charge
- * Fast switching capability
- * Avalanche energy specified

SYMBOL

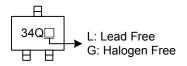


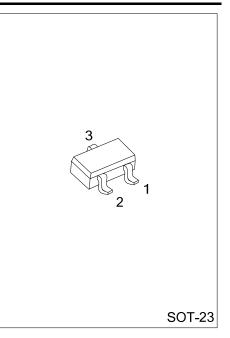
ORDERING INFORMATION

Ordering Number		Deekege	Pin Assignment			Deaking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UT3414L-AE3-R	UT3414G-AE3-R	SOT-23	S	G	D	Tape Reel	



MARKING





■ **ABSOLUTE MAXIMUM RATINGS** (T_a = 25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GSS}	±8	V
Continuous Drain Current	I _D	4.2	Α
Pulsed Drain Current	I _{DM}	15	Α
Power Dissipation	PD	1.4	W
Junction Temperature	TJ	+150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse width limited by $T_{J\left(\text{MAX}\right)}$

THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient	θ_{JA}		100	125	°C/W

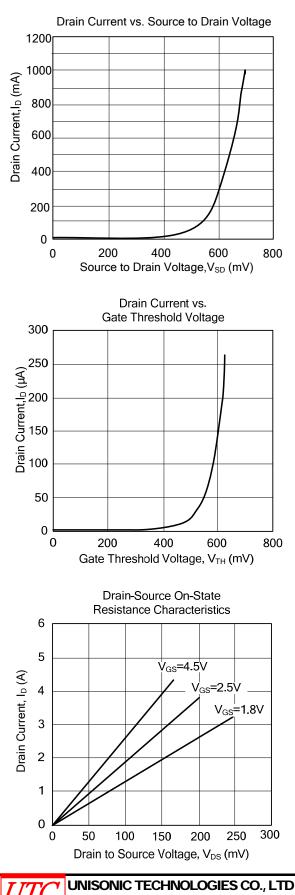
ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS			_			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250µA	20			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =16V, V _{GS} =0V			1	μA
Gate-Source Leakage Current	I _{GSS}	$V_{DS}=0V, V_{GS}=\pm 8V$			100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250µA	0.4	0.6	1	V
On State Drain Current	I _{D(ON)}	V _{DS} =5V, V _{GS} =4.5V	15			Α
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =4.2A		41 50		
		V _{GS} =2.5V, I _D =3.7A		52	63	mΩ
		V _{GS} =1.8V, I _D =3.2A		67	87	<u> </u>
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}			436		pF
Output Capacitance	C _{oss}	V _{DS} =10V, V _{GS} =0V, f=1.0MHz		66		pF
Reverse Transfer Capacitance	C _{RSS}			44		pF
SWITCHING PARAMETERS						
Turn ON Delay Time	t _{D(ON)}			5.5		ns
Turn ON Rise Time	t _R	V_{DS} =10V, V_{GS} =5V, R _L =2.7 Ω		6.3		ns
Turn OFF Delay Time	t _{D(OFF)}	R _G =6Ω		40		ns
Turn OFF Fall-Time	t _F			12.7		ns
Total Gate Charge	Q_{G}			6.2		nC
Gate Source Charge	Q _{GS}	V _{DS} =10V, I _D =4.2A, V _{GS} =4.5V		1.6		nC
Gate Drain Charge	Q _{GD}			0.5		nC
SOURCE- DRAIN DIODE RATINGS A	ND CHARAC	CTERISTICS				
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =1A		0.76	1	V
Maximum Body-Diode Continuous Current	Is				2	А
Body Diode Reverse Recovery Time	t _{RR}	I _F =4A, dI/dt=100A/µs		12.3		ns
Body Diode Reverse Recovery Charge	Q _{RR}	l _F =4A, dl/dt=100A/µs		3.5		nC



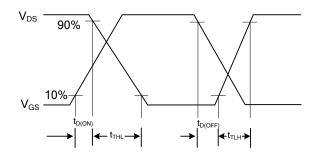
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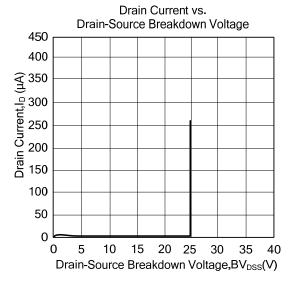
TYPICAL CHARACTERISTICS



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Switching Time Waveforms





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